

REMARKS

Enclosed is a set of four (4) sheets of informal drawings, which have been labeled "ANNOTATED, MARKED-UP DRAWINGS". Changes are being made only to Sheet 3 of the drawings. Proposed changes to Sheet 3 are shown in red ink. In particular, Sheet 3 shows three distinct figures. These three distinct figures were originally labeled together as Figure 3. On the marked-up, amended Sheet 3 submitted herewith, applicants have re-labeled the three distinct figures as Figures 3A, 3B, and 3C.

Applicants' specification has been amended accordingly, as set forth above, to include references to Figures 3A, 3B, and 3C.

Further, applicants have amended Figure 3C to add reference numeral 336, which indicates the schematic top-view of a substrate including several TFT structures of the kind which is illustrated in Figure 3B. The schematic top-view 336 was described at page 17, lines 22 - 23, of applicants' originally filed specification, but reference numeral 336 was inadvertently omitted from the original Figure 3.

Applicants have also amended Figure 3C to correct a labeling error which was present in the original figure. On the original Figure 3C, the elements identified using reference numeral 305 should have been labeled with reference numeral 304. Applicants have therefore amended Figure 3C to change each occurrence of reference numeral 305 to reference numeral 304. This amendment is being made for the purpose of correcting a technical error in the numbering of elements on Figure 3C which is not related to the novel and inventive portion of applicants' claimed invention. According to Paragraph [0063], at page 18, lines 19 - 22, of applicants' originally filed specification: "In the seventh step in the process, "n<sup>+</sup> a-Si Etch-Back", the portion of the "n<sup>+</sup> a-Si layer 305 which was exposed by the patterned dry etch in the sixth step is etched back using techniques known in the art. "n<sup>+</sup> a-Si layer 305 is etched completely through, and is "overetched" into underlying layer 304 of a-Si." Since n<sup>+</sup> a-Si layer 305 would have been etched completely through, n<sup>+</sup> a-Si layer 305 should not be shown in Figure 3C, and the layer that is actually shown is the underlying a-Si layer

304, which has been exposed upon etchback of the n+ a-Si layer 305. The correction to the drawing is necessary to correctly depict the structure resulting after n+ a-Si layer etchback.

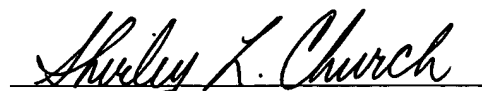
Applicants contend that the amendments to the specification and drawings set forth above are fully supported by applicants' originally submitted specification and drawings, and that no new matter has been added to the application as a result of these amendments.

Enclosed herewith are duplicate sets of five (5) sheets of formal drawings, which incorporate the changes to Figure 3 described above and which are shown on the marked-up, amended Sheet 3 of the informal drawings. If applicants' proposed amendments to the drawings and specification are acceptable to the Examiner, the Examiner is respectfully requested to replace the informal drawings with the formal drawings enclosed herewith. If applicants' proposed amendments are not acceptable to the Examiner, the Examiner is respectfully requested to contact applicants' attorney at the phone number listed below as soon as possible.

Applicants contend that the presently pending claims are in condition for allowance, and the Examiner is respectfully requested to enter the requested amendments and to pass the application to allowance.

The Examiner is invited to contact applicants' attorney with any questions or suggestions, at the telephone number provided below.

Respectfully submitted,

A handwritten signature in cursive script, reading "Shirley L. Church", written over a horizontal line.

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-- ANNOTATED, MARKED-UP DRAWINGS --

Inventor: Soo Young Choi et al.  
Serial No.: 10/829,016  
Title: Controlling the Properties and Uniformity . . .  
Docket No. : AM-9230  
Phone: S. L. Church

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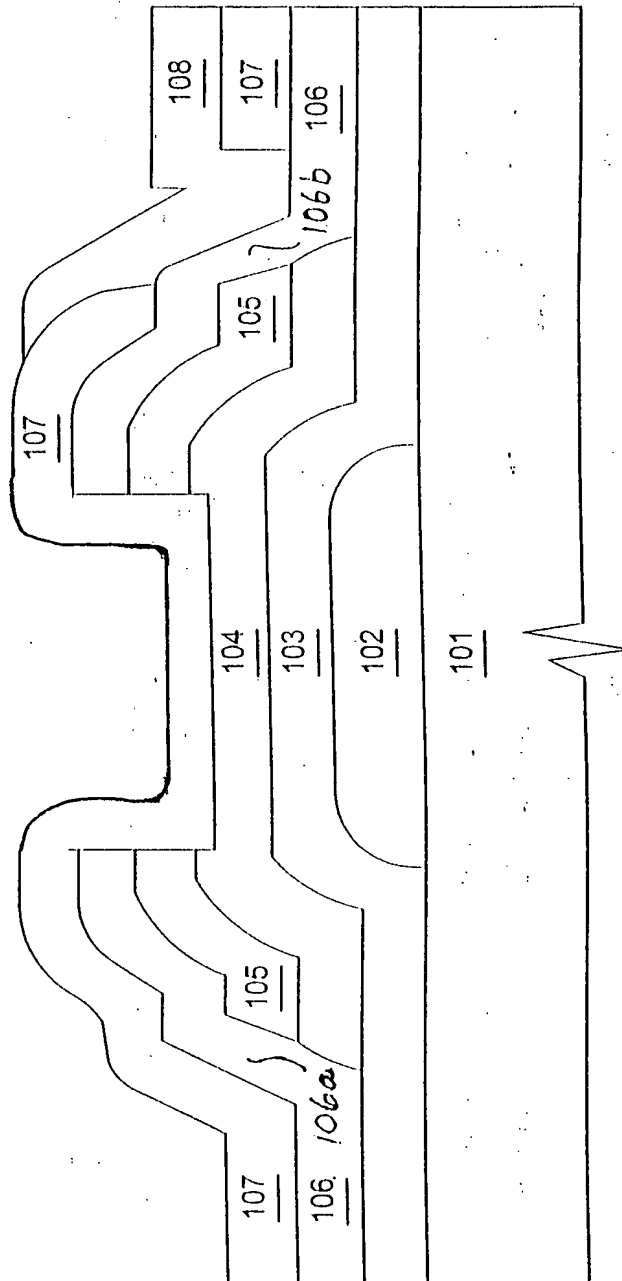


FIG. 1 (Prior Art)

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- ITO Pattern(MASK5)
- ITO Sputtering
- Passivation Etch (MASK4)
- SiNx PECVD
- n+ a-Si Etch-Back
- S/D Pattern(MASK3)
- S/D Sputtering
- a-Si Pattern(MASK2)
- n+a-Si/a-Si/SiNx PECVD
- Gate Pattern(MASK 1)
- Gate Metal Sputtering

300

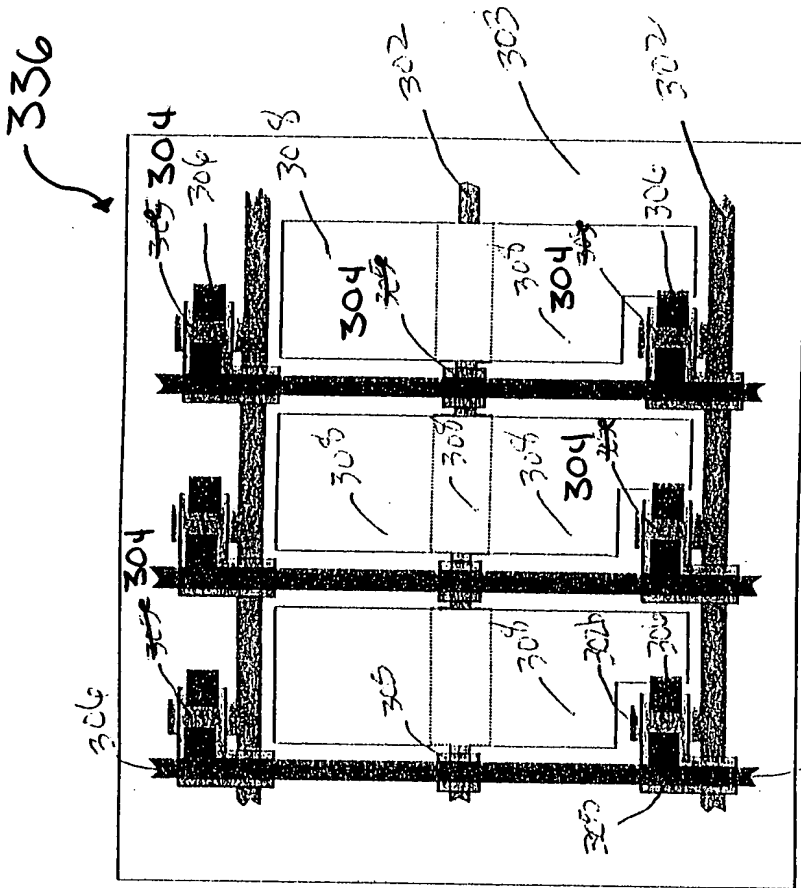


FIG. 3C

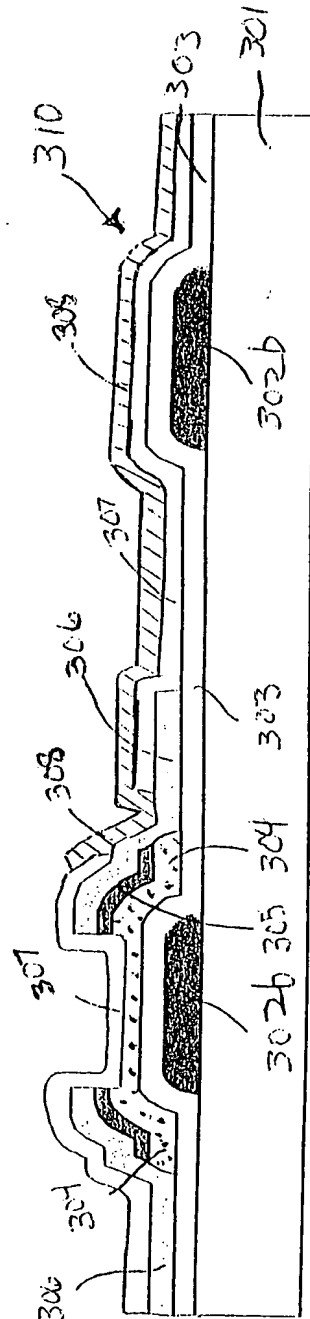


Fig. 3B

FIG. 3A

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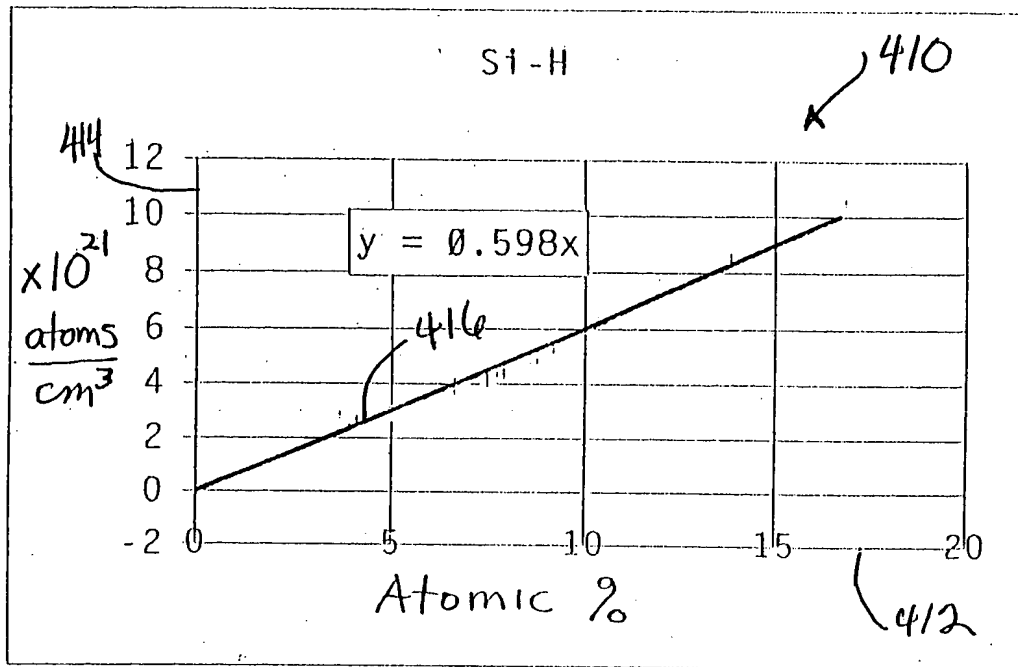


Fig. 4A

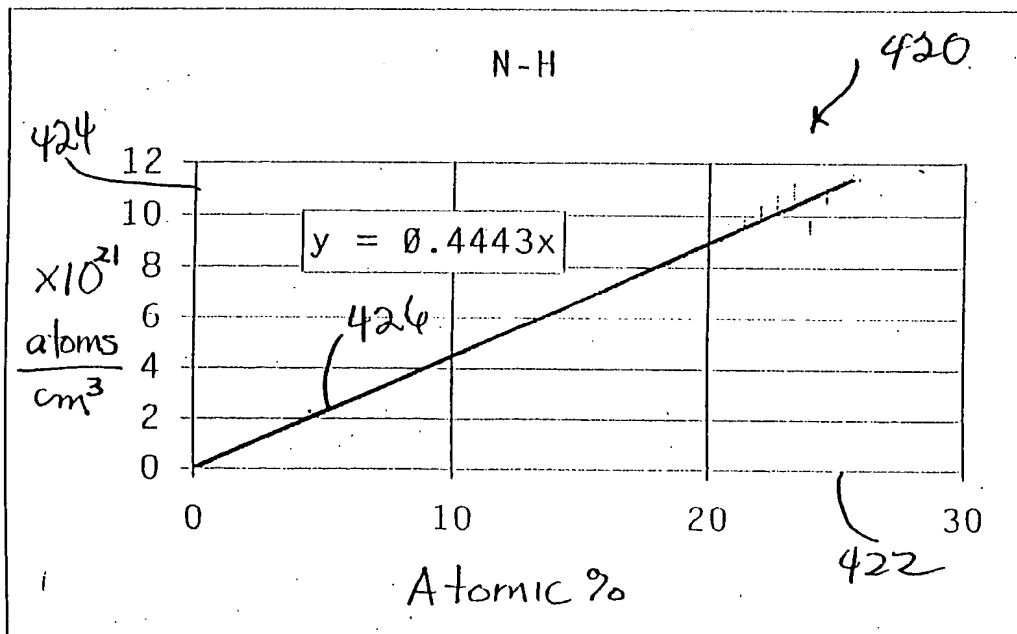


Fig. 4B